Low Voltage Precision Adjustable Shunt Regulator

TLV431, NCV431, SCV431

The TLV431A, B and C series are precision low voltage shunt regulators that are programmable over a wide voltage range of 1.24 V to 16 V. The TLV431A series features a guaranteed reference accuracy of $\pm 1.0\%$ at 25°C and $\pm 2.0\%$ over the entire industrial temperature range of -40°C to 85°C. The TLV431B series features higher reference accuracy of $\pm 0.5\%$ and $\pm 1.0\%$ respectively. For the TLV431C series, the accuracy is even higher. It is $\pm 0.2\%$ and $\pm 1.0\%$ respectively. These devices exhibit a sharp low current turn-on characteristic with a low dynamic impedance of 0.20 Ω over an operating current range of 100 μ A to 20 mA. This combination of features makes this series an excellent replacement for zener diodes in numerous applications circuits that require a precise reference voltage. When combined with an optocoupler, the TLV431A/B/C can be used as an error amplifier for controlling the feedback loop in isolated low output voltage (3.0 V to 3.3 V) switching power supplies. These devices are available in economical TO-92-3 and micro size TSOP-5 and SOT-23-3 packages.

Features

- Programmable Output Voltage Range of 1.24 V to 16 V
- Voltage Reference Tolerance ±1.0% for A Series, ±0.5% for B Series and ±0.2% for C Series
- Sharp Low Current Turn-On Characteristic
- Low Dynamic Output Impedance of 0.20Ω from $100 \mu A$ to 20 mA
- Wide Operating Current Range of 50 μA to 20 mA
- Micro Miniature TSOP-5, SOT-23-3 and TO-92-3 Packages
- NCV and SCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Applications

- Low Output Voltage (3.0 V to 3.3 V) Switching Power Supply Error Amplifier
- Adjustable Voltage or Current Linear and Switching Power Supplies
- Voltage Monitoring
- Current Source and Sink Circuits
- Analog and Digital Circuits Requiring Precision References
- Low Voltage Zener Diode Replacements

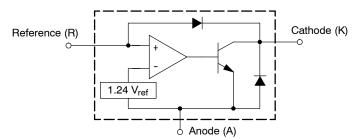
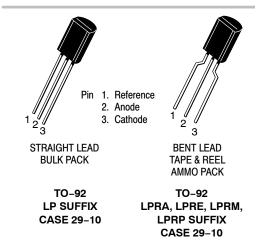


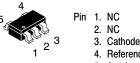
Figure 1. Representative Block Diagram

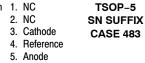


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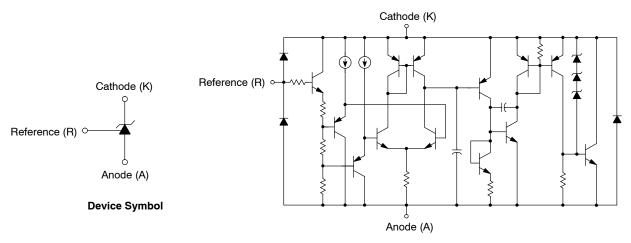
Pin	2.	Reference Cathode Anode	SOT-23 SN1 SUFFIX CASE 318

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.

DEVICE MARKING INFORMATION AND PIN CONNECTIONS

See general marking information in the device marking section on page 13 of this data sheet.



The device contains 13 active transistors.

Figure 2. Representative Device Symbol and Schematic Diagram

MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted)

Rating	Symbol	Value	Unit
Cathode to Anode Voltage	V _{KA}	18	V
Cathode Current Range, Continuous	Ι _Κ	-20 to 25	mA
Reference Input Current Range, Continuous	I _{ref}	-0.05 to 10	mA
Thermal Characteristics LP Suffix Package, TO-92-3 Package		170	°C/W
Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case SN Suffix Package, TSOP-5 Package	$R_{ heta JC}$	178 83	
Thermal Resistance, Junction-to-Ambient SN1 Suffix Package, SOT-23-3 Package	$R_{ hetaJA}$	226	
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	491	
Operating Junction Temperature	T _J	150	°C
Operating Ambient Temperature Range NCV431, S	TLV431 T _A CV431	- 40 to 85 - 40 to 125	°C
Storage Temperature Range	T _{stg}	- 65 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: This device series contains ESD protection and exceeds the following tests:

Human Body Model 2000 V per JEDEC JESD22-A114F, Machine Model Method 200 V per JEDEC JESD22-A115C,

Charged Device Method 1000 V per JEDEC JESD22-C101E. This device contains latch-up protection and exceeds ± 100 mA per JEDEC standard JESD78.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta,JA}}$$

RECOMMENDED OPERATING CONDITIONS

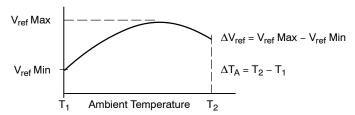
Condition	Symbol	Min	Max	Unit
Cathode to Anode Voltage	V _{KA}	V _{ref}	16	V
Cathode Current	I _K	0.1	20	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		TLV431A		7	TLV431E	3		
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $(V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C})$ $(T_A = T_{low} \text{ to } T_{high}, \text{ Note 1})$	V _{ref}	1.228 1.215	1.240	1.252 1.265	1.234 1.228	1.240	1.246 1.252	٧
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_A = T_{low} \text{ to } T_{high}, \text{ Notes 1, 2, 3)}$	ΔV_{ref}	-	7.2	20	-	7.2	20	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $ (V_{KA} = V_{ref} \text{ to 16 V, I}_{K} = 10 \text{ mA}) $	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	_	-0.6	-1.5	-	-0.6	-1.5	mV V
Reference Terminal Current (Figure 4) (I _K = 10 mA, R1 = 10 k Ω , R2 = open)	I _{ref}	-	0.15	0.3	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I _K = 10 mA, R1 = 10 k Ω , R2 = open, Notes 1, 2, 3)	Δl_{ref}	-	0.04	0.08	-	0.04	0.08	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I _{K(min})	-	30	80	_	30	80	μΑ
Off–State Cathode Current (Figure 5) $ (V_{KA} = 6.0 \text{ V}, V_{ref} = 0) $ $ (V_{KA} = 16 \text{ V}, V_{ref} = 0) $	I _{K(off)}	_ _	0.01 0.012	0.04 0.05	- -	0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) $(V_{KA} = V_{ref}, I_K = 0.1 \text{mA to 20 mA, f} \leq 1.0 \text{kHz, Note 4})$	Z _{KA}	-	0.25	0.4	-	0.25	0.4	Ω

- 1. Ambient temperature range: $T_{low} = -40^{\circ}C$, $T_{high} = 85^{\circ}C$. 2. Guaranteed but not tested.
- 3. The deviation parameters ΔV_{ref} and ΔI_{ref} are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage, αV_{ref} is defined as:

$$\alpha V_{ref} \left(\frac{ppm}{^{\circ}C} \right) = \frac{\left(\frac{(\Delta V_{ref})}{V_{ref} \left(T_{A} = 25^{\circ}C \right)} \times 10^{6} \right)}{\Delta T_{A}}$$

αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature, refer to Figure 8. Example: $\Delta V_{ref} = 7.2 \text{ mV}$ and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V ΔT_A = 125°C

$$\alpha V_{ref} \left(\frac{ppm}{{}^{\circ}C} \right) = \frac{0.0072}{1.241} \times 10^{6} = 46 \text{ ppm/}^{\circ}C$$

4. The dynamic impedance $Z_{\mbox{\scriptsize KA}}$ is defined as:

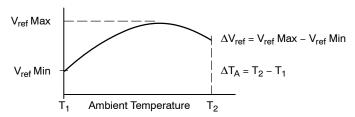
$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

			TLV431C		
Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = T_{low} \text{ to } T_{high}, \text{ Note 5}) $	V _{ref}	1.237 1.228	1.240	1.243 1.252	V
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = T_{low} \text{ to } T_{high}, \text{ Notes 5, 6, 7)}$	ΔV_{ref}	-	7.2	20	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to } 16 \text{ V}, I_K = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	-	-0.6	-1.5	mV V
Reference Terminal Current (Figure 4) (I _K = 10 mA, R1 = 10 k Ω , R2 = open)	I _{ref}	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I _K = 10 mA, R1 = 10 k Ω , R2 = open, Notes 5, 6, 7)	ΔI_{ref}	-	0.04	0.08	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I _{K(min})	-	30	80	μΑ
Off-State Cathode Current (Figure 5) (V _{KA} = 6.0 V, V _{ref} = 0) (V _{KA} = 16 V, V _{ref} = 0)	I _{K(off)}		0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) $ (V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA, } f \leq 1.0 \text{ kHz, Note 8}) $	Z _{KA}	-	0.25	0.4	Ω

- 5. Ambient temperature range: $T_{low} = -40^{\circ}C$, $T_{high} = 85^{\circ}C$. 6. Guaranteed but not tested.
- The deviation parameters ΔV_{ref} and ΔI_{ref} are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage, αV_{ref} is defined as:

$$\alpha V_{ref} \, \left(\frac{ppm}{^{\circ}C} \right) = \frac{\left(\frac{(\Delta V_{ref})}{V_{ref} \, \left(T_{A} = 25^{\circ}C \right)} \times \, 10^{6} \right)}{\Delta T_{A}}$$

 αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature, refer to Figure 8. Example: $\Delta V_{ref} = 7.2 \text{ mV}$ and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V ΔT_A = 125°C

$$\alpha V_{ref} \left(\frac{ppm}{{}^{\circ}C} \right) = \frac{\frac{0.0072}{1.241} \times 10^{6}}{125} = 46 \text{ ppm}/{}^{\circ}C$$

8. The dynamic impedance Z_{KA} is defined as:

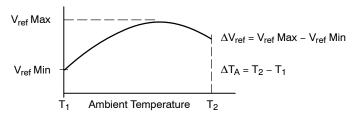
$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted. NCV prefix indicates TSOP package device. SCV prefix indicates SOT–23 package device.)

		NCV431A, SCV431A			
Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $(V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C})$ $(T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C})$ $(T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C})$	V _{ref}	1.228 1.215 1.211	1.240 - -	1.252 1.265 1.265	V
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C}, \text{ Notes } 9, 10)$ $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \text{ Notes } 9, 10)$	ΔV_{ref}	<u>-</u>	7.2 7.2	20 24	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to 16 V}, I_{K} = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	-	-0.6	-1.5	$\frac{\text{mV}}{\text{V}}$
Reference Terminal Current (Figure 4) ($I_K = 10 \text{ mA}, R1 = 10 \text{ k}\Omega, R2 = \text{open}$)	I _{ref}	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) $ (I_K=10 \text{ mA}, R1=10 \text{ k}\Omega, R2=\text{open}, T_A=-40^{\circ}\text{C to }85^{\circ}\text{C}, \text{Notes }9, 10) \\ (I_K=10 \text{ mA}, R1=10 \text{ k}\Omega, R2=\text{open}, T_A=-40^{\circ}\text{C to }125^{\circ}\text{C}, \text{Notes }9, 10) $	ΔI_{ref}	_ _	0.04	0.08 0.10	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I _{K(min)}	_	30	80	μΑ
Off-State Cathode Current (Figure 5) (V _{KA} = 6.0 V, V _{ref} = 0) (V _{KA} = 16 V, V _{ref} = 0)	I _{K(off)}	- -	0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) ($V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA, } f \le 1.0 \text{ kHz, Note } 11$)	Z _{KA}	_	0.25	0.4	Ω

^{9.} Guaranteed but not tested.

^{10.} The deviation parameters ΔV_{ref} and ΔI_{ref} are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage, $\alpha \text{V}_{\text{ref}}$ is defined as:

$$\alpha V_{ref} \left(\frac{ppm}{^{\circ}C} \right) = \frac{\left(\frac{(\Delta V_{ref})}{V_{ref} \left(T_{A} = 25^{\circ}C \right)} \times 10^{6} \right)}{\Delta T_{\Delta}}$$

 αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature, refer to Figure 8.

Example: ΔV_{ref} = 7.2 mV and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V ΔT_A = 125°C

$$\alpha V_{\mbox{ref}} \left(\frac{\mbox{ppm}}{^{\circ}\mbox{C}} \right) = \frac{0.0072}{1.241} \times 10^{6} \\ = 46 \ \mbox{ppm}/^{\circ}\mbox{C}$$

11. The dynamic impedance Z_{KA} is defined as:

$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

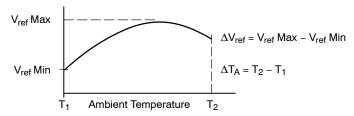
$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted. NCV prefix indicates TSOP package device. SCV prefix indicates SOT-23 package device.)

		NCV43	31B, SC	V431B	
Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}) $	V _{ref}	1.234 1.228 1.224	1.240 - -	1.246 1.252 1.252	\ \
Reference Input Voltage Deviation Over Temperature (Figure 3) $ (V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C}, \text{ Notes } 9, 10) \\ (V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \text{ Notes } 9, 10) $	ΔV_{ref}	- -	7.2 7.2	20 24	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to } 16 \text{ V}, I_{K} = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	-	-0.6	-1.5	$\frac{\text{mV}}{\text{V}}$
Reference Terminal Current (Figure 4) (I _K = 10 mA, R1 = 10 k Ω , R2 = open)	I _{ref}	_	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) $ (I_K=10 \text{ mA}, \text{ R1}=10 \text{ k}\Omega, \text{ R2}=\text{open}, T_A=-40^{\circ}\text{C to } 85^{\circ}\text{C}, \text{ Notes } 12, 13) \\ (I_K=10 \text{ mA}, \text{ R1}=10 \text{ k}\Omega, \text{ R2}=\text{open}, T_A=-40^{\circ}\text{C to } 125^{\circ}\text{C}, \text{ Notes } 12, 13) $	ΔI_{ref}	- -	0.04	0.08 0.10	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I _{K(min})	-	30	80	μΑ
Off-State Cathode Current (Figure 5) (V _{KA} = 6.0 V, V _{ref} = 0) (V _{KA} = 16 V, V _{ref} = 0)	I _{K(off)}		0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) $(V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA}, f \leq 1.0 \text{ kHz}, \text{ Note } 14)$	Z _{KA}	_	0.25	0.4	Ω

^{12.} Guaranteed but not tested.

^{13.} The deviation parameters ΔV_{ref} and ΔI_{ref} are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage, αV_{ref} is defined as:

$$\alpha V_{ref} \left(\frac{ppm}{^{\circ}C} \right) = \frac{\left(\frac{(\Delta V_{ref})}{V_{ref} \left(T_{A} = 25^{\circ}C \right)} \times 10^{6} \right)}{\Delta T_{\Delta}}$$

 αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature, refer to Figure 8.

Example: ΔV_{ref} = 7.2 mV and the slope is positive, V_{ref} @ 25°C = 1.241 V ΔT_A = 125°C

$$\alpha V_{ref} \left(\frac{ppm}{^{\circ}C} \right) = \frac{0.0072 \times 10^{6}}{1.241} = 46 \; ppm/^{\circ}C$$

14. The dynamic impedance $Z_{\mbox{\scriptsize KA}}$ is defined as:

$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

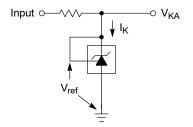


Figure 3. Test Circuit for V_{KA} = V_{ref}

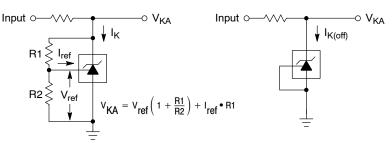


Figure 4. Test Circuit for $V_{KA} > V_{ref}$

Figure 5. Test Circuit for I_{K(off)}

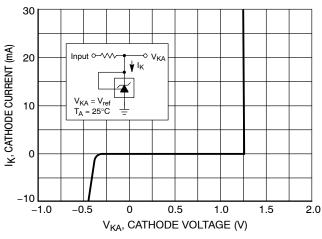


Figure 6. Cathode Current vs. Cathode Voltage

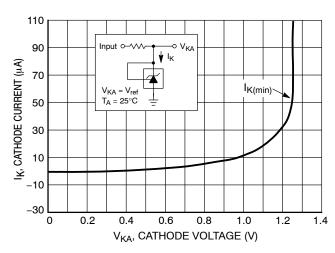


Figure 7. Cathode Current vs. Cathode Voltage

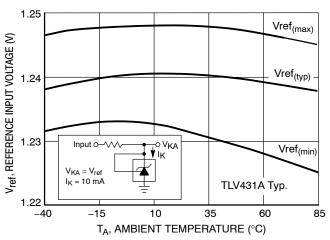


Figure 8. Reference Input Voltage versus
Ambient Temperature

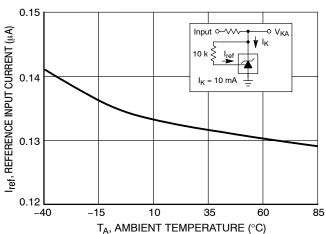
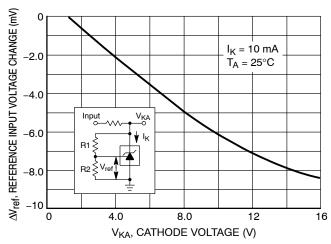


Figure 9. Reference Input Current versus Ambient Temperature

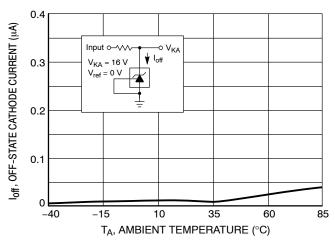


4.0

(Val 16 V Vref = 0 V Vref =

Figure 10. Reference Input Voltage Change versus Cathode Voltage

Figure 11. Off-State Cathode Current versus Cathode Voltage



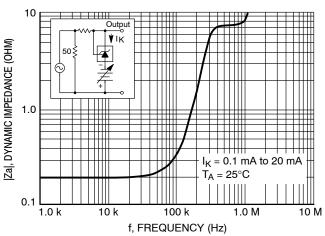
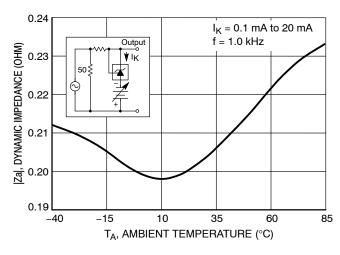


Figure 12. Off-State Cathode Current versus
Ambient Temperature

Figure 13. Dynamic Impedance versus Frequency



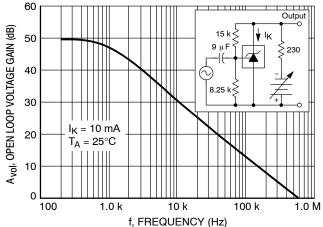
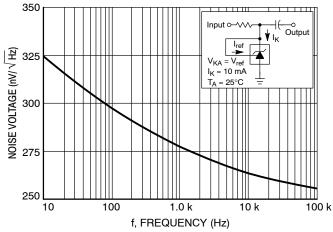


Figure 14. Dynamic Impedance versus

Ambient Temperature

Figure 15. Open-Loop Voltage Gain versus Frequency



f, FREQUENCY (Hz)

Figure 16. Spectral Noise Density

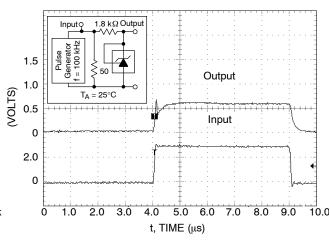


Figure 17. Pulse Response

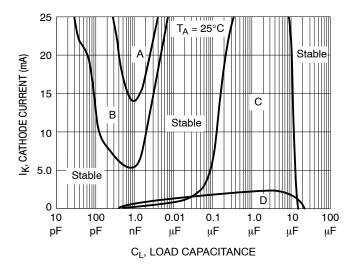
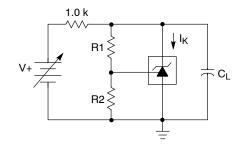


Figure 18. Stability Boundary Conditions



Unstable Regions	V _{KA} (V)	R1 (kΩ)	R2 (kΩ)
A, C	V_{ref}	0	8
B, D	5.0	30.4	10

Figure 19. Test Circuit for Figure 18

Stability

Figures 18 and 19 show the stability boundaries and circuit configurations for the worst case conditions with the load capacitance mounted as close as possible to the device. The required load capacitance for stable operation can vary depending on the operating temperature and capacitor

equivalent series resistance (ESR). Ceramic or tantalum surface mount capacitors are recommended for both temperature and ESR. The application circuit stability should be verified over the anticipated operating current and temperature ranges.

TYPICAL APPLICATIONS

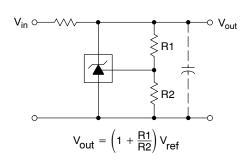
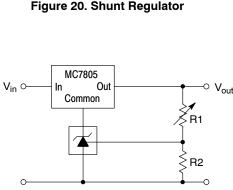


Figure 20. Shunt Regulator



$$V_{\text{out}} = \left(1 + \frac{\text{R1}}{\text{R2}}\right) V_{\text{ref}}$$

$$V_{\text{out}(\text{min})} = V_{\text{ref}} + 5.0 \text{ V}$$

Figure 22. Output Control for a Three Terminal Fixed Regulator

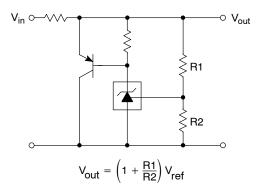


Figure 21. High Current Shunt Regulator

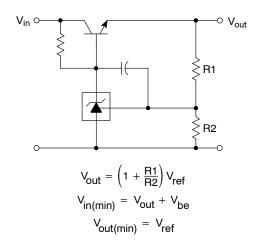


Figure 23. Series Pass Regulator

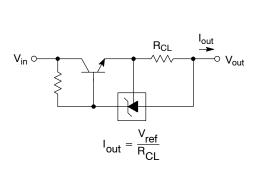


Figure 24. Constant Current Source

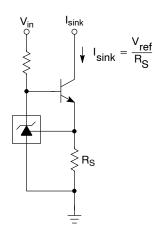


Figure 25. Constant Current Sink

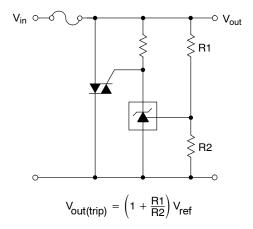


Figure 26. TRIAC Crowbar

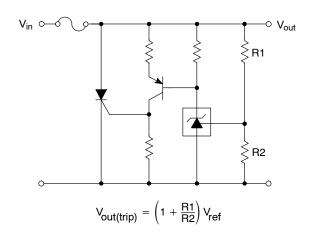
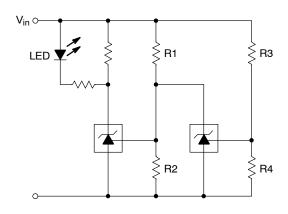


Figure 27. SCR Crowbar



 $\label{eq:L.E.D.} \text{L.E.D. indicator is 'ON' when } V_{in} \text{ is between the upper and lower limits,}$

$$\begin{aligned} & \text{Lower limit} = \left(1 + \frac{R1}{R2}\right) V_{ref} \\ & \text{Upper limit} = \left(1 + \frac{R3}{R4}\right) V_{ref} \end{aligned}$$

Figure 28. Voltage Monitor

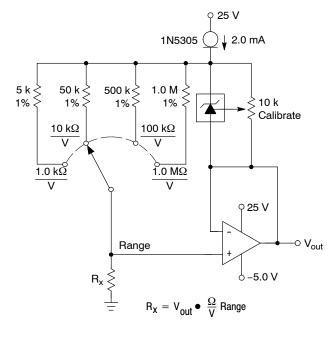


Figure 29. Linear Ohmmeter

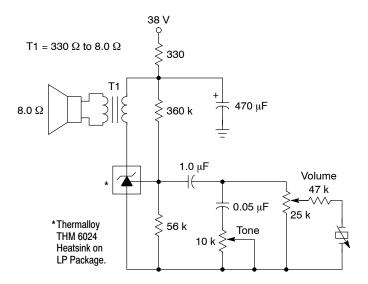


Figure 30. Simple 400 mW Phono Amplifier

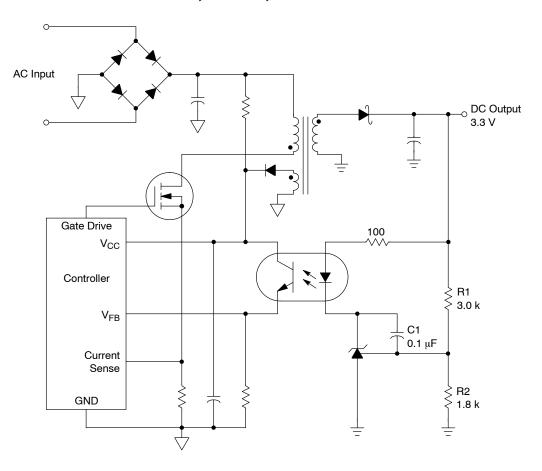
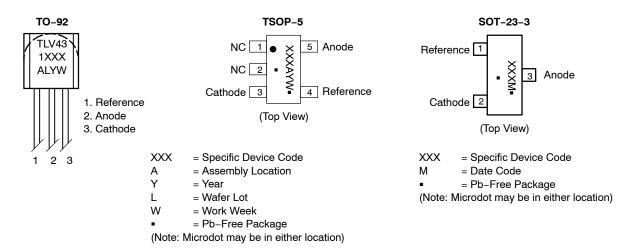


Figure 31. Isolated Output Line Powered Switching Power Supply

The above circuit shows the TLV431A/B/C as a compensated amplifier controlling the feedback loop of an isolated output line powered switching regulator. The output voltage is programmed to 3.3 V by the resistors values selected for R1 and R2. The minimum output voltage that can be programmed with this circuit is 2.64 V, and is limited by the sum of the reference voltage (1.24 V) and the forward drop of the optocoupler light emitting diode (1.4 V). Capacitor C1 provides loop compensation.

PIN CONNECTIONS AND DEVICE MARKING

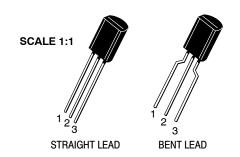


ORDERING INFORMATION

Device	Device Code	Package	Shipping [†]
TLV431ALPG	ALP	TO-92-3 (Pb-Free)	6000 / Box
TLV431ALPRAG	ALP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431ALPREG	ALP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431ALPRMG	ALP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431ALPRPG	ALP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431ASNT1G	RAA	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431ASN1T1G	RAF	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431BLPG	BLP	TO-92-3 (Pb-Free)	6000 / Box
TLV431BLPRAG	BLP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431BLPREG	BLP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431BLPRMG	BLP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431BLPRPG	BLP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431BSNT1G	RAH	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431BSN1T1G	RAG	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431CSN1T1G	AAN	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
SCV431ASN1T1G*	RAE	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
SCV431BSN1T1G*	RAC	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
NCV431ASNT1G*	ACH	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
NCV431BSNT1G*	AD6	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*SCV, NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and

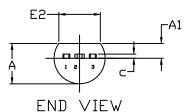
PPAP Capable.

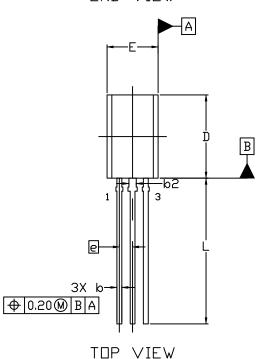


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

STRAIGHT LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Δ	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
Ø	0.38	0.465	0.55		
ρQ	0.62	0.70	0.78		
C	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E2	3.90				
е	1.27 BSC				
L	13.80	14.00	14.20		

STYLES AND MARKING ON PAGE 3

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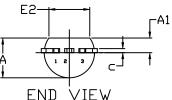
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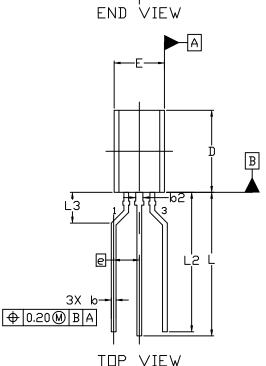


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Α	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
q	0.38	0.465	0.55		
b2	0.62	0.70	0.78		
C	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E2	3.90				
u		2.50 BSC			
Г	13.80	14.00	14.20		
L2	13.20	13.60	14.00		
L3	·	3.00 REF			

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TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

DATE 05 MAR 2021

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
	CATE	DIM 4		2.	DRAIN	PIN 1. 2.		2.	CATHODE GATE ANODE
2.	CATHODE & ANODE	2.		2.	ANODE 1	2.	EMITTER		
2.	ANODE	PIN 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.			GATE	PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	
	V _{CC}	2.	MT	2.	CATHODE	PIN 1. 2.	NOT CONNECTED ANODE CATHODE		DRAIN GATE SOURCE
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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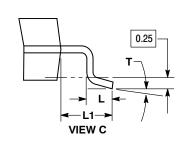


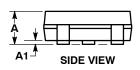
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

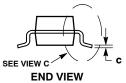
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

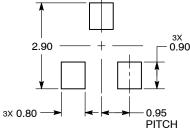
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

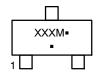
3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	5. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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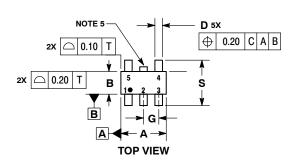
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3. CATHODE



TSOP-5 **CASE 483 ISSUE N**

DATE 12 AUG 2020







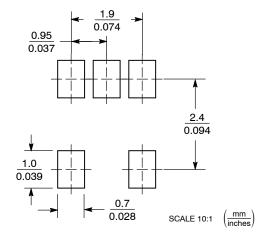


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE
 MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
C	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2 50	3.00		

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code

= Year = Pb-Free Package

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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X60003CIG3-41 X60003DIG3Z-41T1 X60250V8I REF3025TB-GT3 TL431CPG LT1027CCS8-5#TRPBF AD587KRZ-REEL CA-HP6025S CA-HP6041S LT1236BCS8-5#TRPBF ADR435BRMZ-REEL7 CA-HP6050S MC1403BN LM285Z-2.5 LM385B-ADJ LM385B-2.5 HT385R-1.2 HT336R-2.5 TL431L REF6050IDGKR TL431APA LM385D-1.2RG MC1403BDRG LT6657AHMS8-2.5#TRPBF LM236D-2.5RG LM336LP-5.0G LM336D-5.0RG LM385LP-2.5G LM336D-2.5RG LM385D-2.5RG MAX6225BESA+T MAX875BESA+T LM336LP-2.5G